2N6166

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 2N6166** is Designed to operate in a collector modulated VHF Power Amplifier Applications up to 200 MHz.

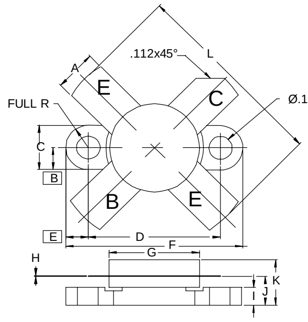
FEATURES:

- η_C = 60 % min. @ 100 W/150 MHz
- P_G = 6.0 dB min. @ 100 W/150 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CBO}	65 V
V_{EBO}	4.0 V
P_{DISS}	117 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W

PACKAGE STYLE .500 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.7.30 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K		.280 / 7.11
L	.980 / 24.89	1.050 / 26.67

ORDER CODE: ASI10790

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 200 mA	65			V
BV_{CEO}	I_C = 200 mA	35			V
BV_{EBO}	I_E = 10 Ma	4.0			V
I_{CES}	V_{CE} = 30 V			5.0	mA
I_{CBO}	V_{CB} = 30 V			30	mA
h_{FE}	V_{CE} = 5.0 V I_C = 500 mA	5.0			---
C_{OB}	V_{CE} = 28 V f = 1.0 MHz			130	pF
P_G	V_{CC} = 28 V P_{OUT} = 100 W f = 150 MHz	6.0			dB
η_C		60			%